Silicon PNP Power Transistors 2SB691

DESCRIPTION

With TO-3PN package

·Wide area of safe operation

APPLICATIONS

·For low frequency power amplifier and power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

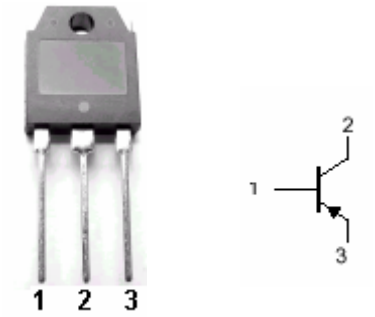

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-130	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
P_C	Collector power dissipation	T_C=25□	60	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-30mA ;I_B=0	-80			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA ;I_E=0	-130			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA ;I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-3A; I_B=-0.3A			-1.5	V
V_{BE}	Base-emitter on voltage	I_C=-1A;V_{CE}=-5V			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-130V; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-0.1	mA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-5V	40		200	
h_{FE-2}	DC current gain	I_C=-3A ; V_{CE}=-5V	20			
f_T	Transition frequency	I_C=-1A ; V_{CE}=-5V		7		MHz

PACKAGE OUTLINE

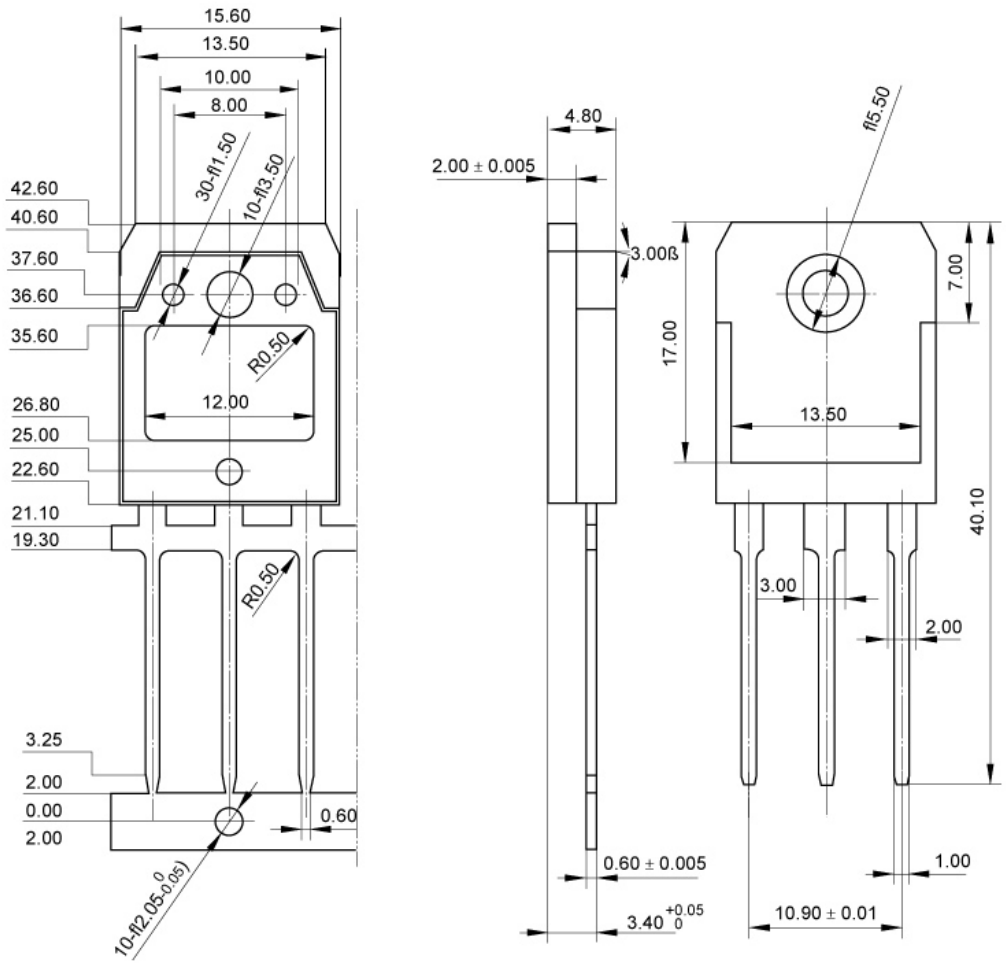

Fig.2 outline dimensions